TOSHIBA FAST RECOVERY DIODE SILICON DIFFUSED TYPE

## 200FXG13, 200FXH13

HIGH SPEED RECTIFIER APPLICATIONS

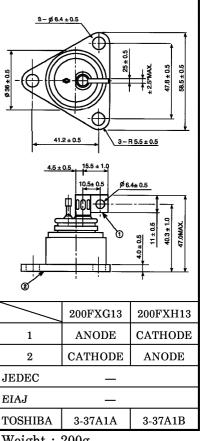
Unit in mm

Repetitive Peak Reverse Voltage  $: V_{RRM} = 3000V$ Average Forward Current  $: I_{F(AV)} = 200A$ 

Reverse Recovery Time (Tj=25°C) :  $t_{rr}\!=\!4.5\mu s$ 

## **MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	$v_{RRM}$	3000	V	
Non-Repetitive Peak Reverse Voltage (Non-Repetitive $\leq 5$ ms, $T_j = 0 \sim 125$ °C)	V <sub>RSM</sub>	3100	V	
Average Forward Current	I <sub>F (AV)</sub>	200	A	
Peak One Cycle Surge Forward	Inone	4000 (50Hz)	A	
Current	IFSM	4400 (60Hz)		
Junction Temperature Range	$T_{j}$	-40~125	°C	
Storage Temperature Range	$T_{ m stg}$	-40~125	°C	
Screw Torque	_	1.6	N⋅m	



Weight: 200g

## **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	MAX.	UNIT
Repetitive Peak Reverse Current	$I_{RRM}$	$V_{RRM} = 3000V, T_j = 125^{\circ}C$		_	40	mA
Peak Forward Voltage	$ m V_{FM}$	$I_{FM} = 630A \ (T_j = 25^{\circ}C)$			1.8	V
Reverse Recovery Time		$I_{\mathbf{F}} = 200 \mathbf{A}$	$T_j = 25$ °C		4.5	.,,
		$di_{\mathbf{F}}/dt = 100 \mathrm{A}/\mu \mathrm{s}$	$T_j = 125$ °C		5.5	$\mu$ s
Thermal Resistance	R <sub>th (j-c)</sub>	Junction to Case		_	0.16	°C/W

Note: Contact thermal resistance  $R_{th (c-f)} = 0.04$ °C/W (Applied silicone grease)

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